

Ultrafast Soft Recovery Diode, 80 A FRED Pt™


PowerTab™


FEATURES

- Ultrafast recovery
- 175 °C operating junction temperature
- Screw mounting only
- Lead (Pb)-free plating
- Designed and qualified for industrial level
- Compliant to RoHS directive 2002/95/EC


RoHS
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

PRODUCT SUMMARY

t_{rr} (typical)	50 ns
$I_{F(AV)}$	80 A
V_R	400 V

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V_R		400	V
Continuous forward current	$I_{F(AV)}$	$T_C = 101\text{ °C}$	80	A
Single pulse forward current	I_{FSM}	$T_C = 25\text{ °C}$	800	
Maximum repetitive forward current	I_{FRM}	Square wave, 20 kHz	160	
Operating junction and storage temperatures	T_J, T_{Stg}		- 55 to 175	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_r	$I_R = 100\text{ }\mu\text{A}$	400	-	-	V
Forward voltage	V_F	$I_F = 80\text{ A}$	-	1.1	1.3	
		$I_F = 80\text{ A}, T_J = 175\text{ °C}$	-	0.92	1.08	
		$I_F = 80\text{ A}, T_J = 125\text{ °C}$	-	0.98	1.15	
Reverse leakage current	I_R	$V_R = V_R\text{ rated}$	-	-	50	μA
		$T_J = 150\text{ °C}, V_R = V_R\text{ rated}$	-	-	2	mA
Junction capacitance	C_T	$V_R = 200\text{ V}$	-	50	-	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body	-	3.5	-	nH

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time	t_{rr}	$I_F = 1\text{ A}$, $dI_F/dt = 200\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$	-	50	60	ns
		$T_J = 25\text{ }^{\circ}\text{C}$	-	87	-	
		$T_J = 125\text{ }^{\circ}\text{C}$	-	151	-	
Peak recovery current	I_{RRM}	$T_J = 25\text{ }^{\circ}\text{C}$	-	9.3	-	A
		$T_J = 125\text{ }^{\circ}\text{C}$	-	17.2	-	
Reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$	-	405	-	nC
		$T_J = 125\text{ }^{\circ}\text{C}$	-	1300	-	

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R_{thJC}		-	-	0.70	K/W
Thermal resistance, junction to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	
Weight			-	-	5.02	g
			-	0.18	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab™	80EBU04			

Ultrafast Soft Recovery Diode, Vishay High Power Products

80 A FRED P_t[™]

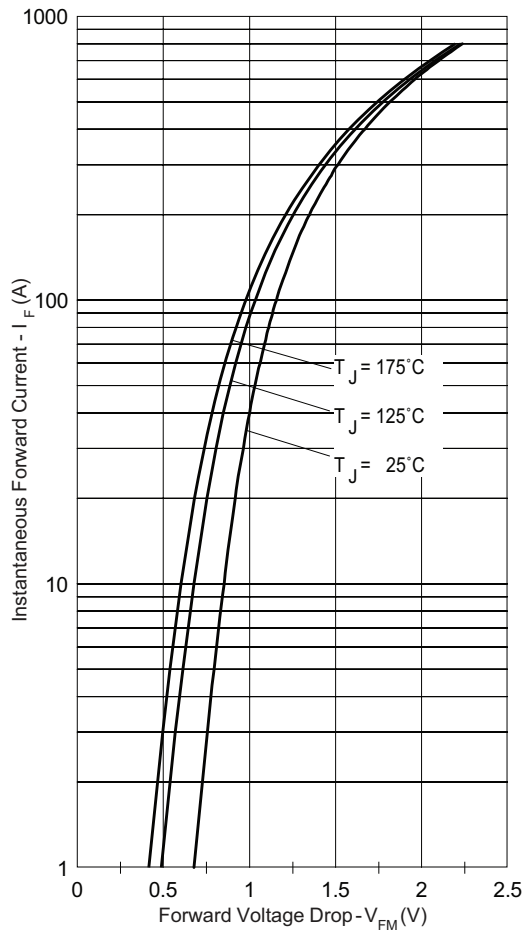


Fig. 1 - Maximum Forward Voltage Drop Characteristics

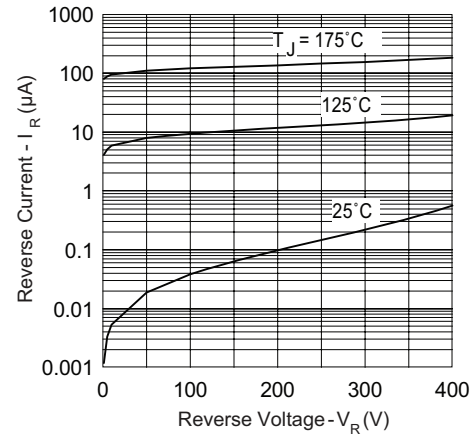


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

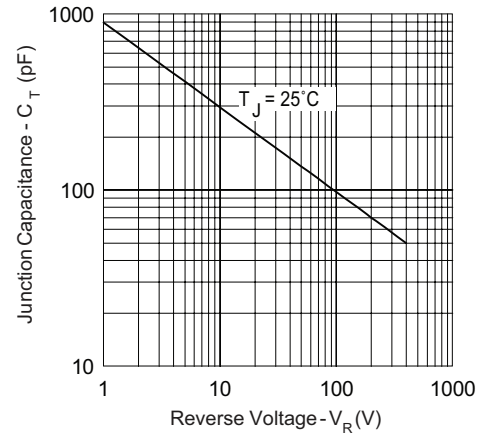


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

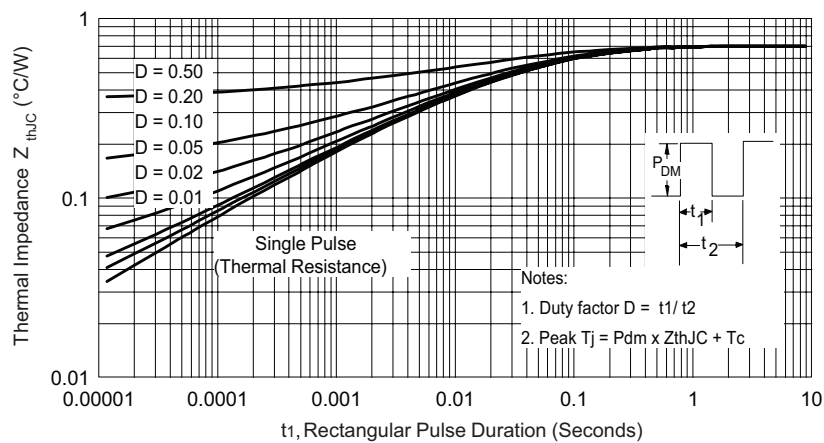


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Vishay High Power Products Ultrafast Soft Recovery Diode, 80 A FRED Pt™

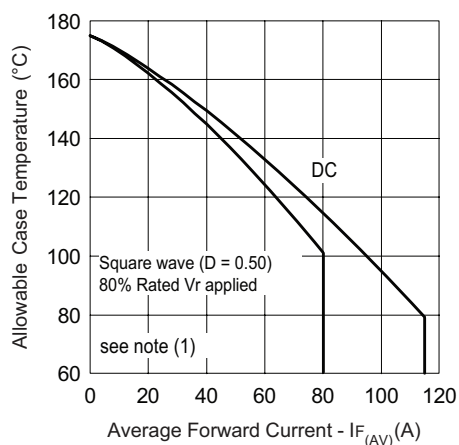


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

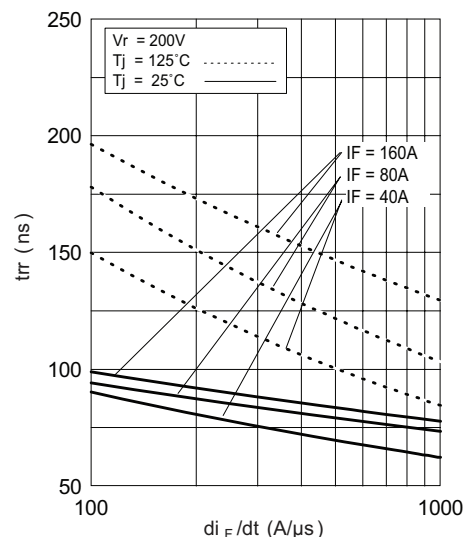


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

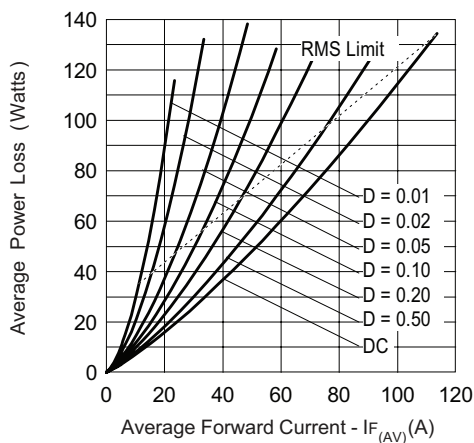


Fig. 6 - Forward Power Loss Characteristics

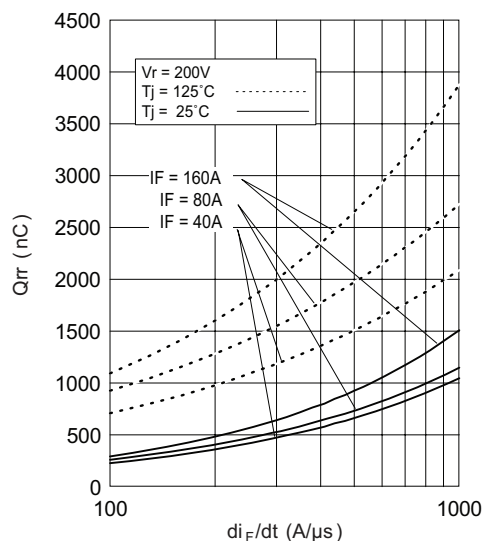


Fig. 8 - Typical Stored Charge vs. dI_F/dt

Note

- (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R

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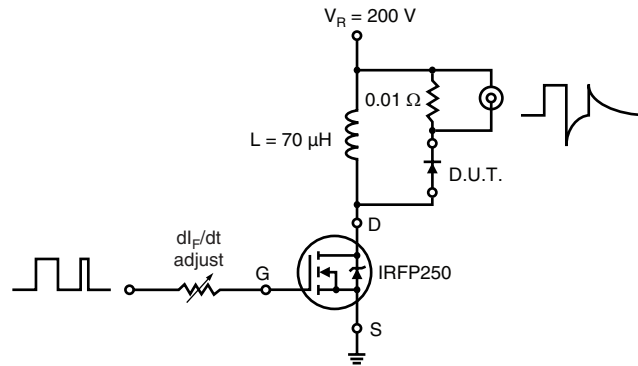
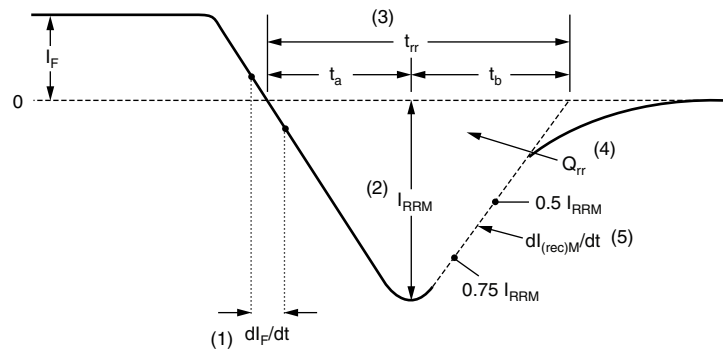


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) di_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.50 I_{RRM}$ extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code	80	E	B	U	04
	①	②	③	④	⑤
①	- Current rating (80 = 80 A)				
②	- Single diode				
③	- PowerTab™ (ultrafast/hyperfast only)				
④	- Ultrafast recovery				
⑤	- Voltage rating (04 = 400 V)				

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95240
Part marking information	www.vishay.com/doc?95370
Application note	www.vishay.com/doc?95179



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